

ABSTRACT OF THE DISCLOSURE

After a MOS transistor is formed on a semiconductor substrate, an Ir film, LT film, PZT film, and IrO₂ film are formed in this order on the entire surface. Although the LT film itself is not a ferroelectric film, a ferroelectric film is formed by a stacked film of the LT film and PZT film. In a ferroelectric capacitor having this ferroelectric film, the LT film does not contain Pb, so the alignment can be readily controlled during the film formation. This raises the alignment of the LT film. The crystal structure of the LT film is a perovskite structure similar to that of the PZT film. Since the PZT film is formed on this LT film, the alignment of the LT film is taken over when the PZT film is grown. This raises the alignment of the PZT film.